

V _{CES}	650V
Ι _{C(100°C)}	20A
V _{CE(sat) (Typ.)}	1.6V
P _D	144W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating ; RoHS Compliant

Applications

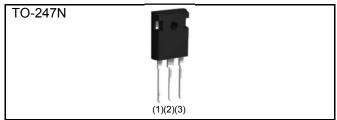
PFC

UPS

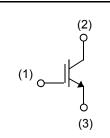
Power Conditioner

IH

Outline



Inner Circuit





Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Tuno	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	450
	Packing code	C11
	Marking	RGTH40TS65

•Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

		,		
Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V _{GES}	±30	V
Collector Current	$T_{\rm C} = 25^{\circ}{\rm C}$	۱ _C	40	А
Collector Current	T _C = 100°C	Ι _C	20	А
Pulsed Collector Current		I _{CP} *1	80	А
Power Dissinction	$T_{\rm C} = 25^{\circ}{\rm C}$	P _D	144	W
Power Dissipation	T _C = 100°C	P _D	72	W
Operating Junction Temperature		Tj	-40 to +175	°C
Storage Temperature		T _{stg}	–55 to +175	°C

*1 Pulse width limited by T_{imax.}

Thermal Resistance

Daramatar	Symbol	Values			Unit
Parameter		Min.	Тур.	Max.	Unit
Thermal Resistance IGBT Junction - Case	$R_{\theta(j\text{-}c)}$	-	-	1.04	°C/W

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit	
Faranieler	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Collector - Emitter Breakdown Voltage	BV _{CES}	I _C = 10μΑ, V _{GE} = 0V	650	-	-	V	
Collector Cut - off Current	I _{CES}	V _{CE} = 650V, V _{GE} = 0V	-	-	10	μA	
Gate - Emitter Leakage Current	I _{GES}	V_{GE} = ±30V, V_{CE} = 0V	-	-	±200	nA	
Gate - Emitter Threshold Voltage	V _{GE(th)}	V _{CE} = 5V, I _C = 13.3mA	4.5	5.5	6.5	V	
Collector - Emitter Saturation Voltage	V _{CE(sat)}	I _C = 20A, V _{GE} = 15V T _j = 25°C T _j = 175°C	-	1.6 2.1	2.1 -	V	

•IGBT Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Deremeter	Cumphal	Operatitiense	Values				
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Input Capacitance	C _{ies}	V _{CE} = 30V	-	1060	-		
Output Capacitance	C _{oes}	V _{GE} = 0V	-	47	-	pF	
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	18	-		
Total Gate Charge	Q_g	V _{CE} = 300V	-	40	-		
Gate - Emitter Charge	Q_{ge}	I _C = 20A	-	9	-	nC	
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	15	-		
Turn - on Delay Time	t _{d(on)}	I _C = 20A, V _{CC} = 400V	-	22	-		
Rise Time	t _r	V _{GE} = 15V, R _G = 10Ω	-	25	-		
Turn - off Delay Time	$t_{d(off)}$	T _j = 25°C	-	73	-	ns	
Fall Time	t _f	Inductive Load	-	48	-		
Turn - on Delay Time	t _{d(on)}	I _C = 20A, V _{CC} = 400V	-	22	-		
Rise Time	t _r	V _{GE} = 15V, R _G = 10Ω	-	25	-		
Turn - off Delay Time	$t_{d(off)}$	T _j = 175°C	-	83	-	ns	
Fall Time	t _f	Inductive Load	-	58	-		
		I _C = 80A, V _{CC} = 520V					
Reverse Bias Safe Operating Area	RBSOA	V _P = 650V, V _{GE} = 15V	FU	LL SQUA	RE	-	
		R _G = 60Ω, T _j = 175°C					

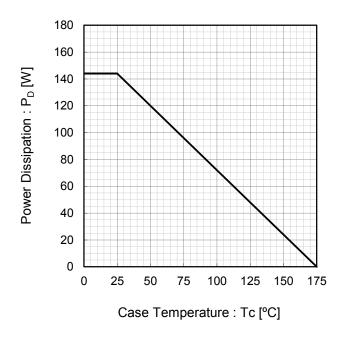


Fig.1 Power Dissipation vs. Case Temperature

Fig.2 Collector Current vs. Case Temperature

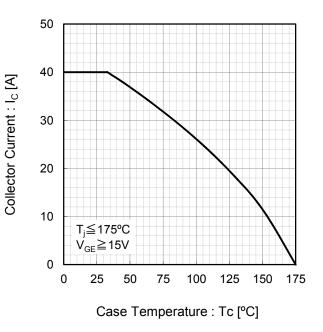
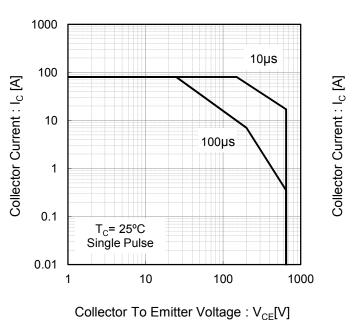
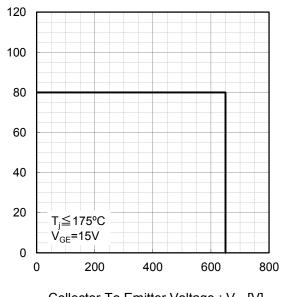


Fig.3 Forward Bias Safe Operating Area

Fig.4 Reverse Bias Safe Operating Area





Collector To Emitter Voltage : $V_{CE}[V]$

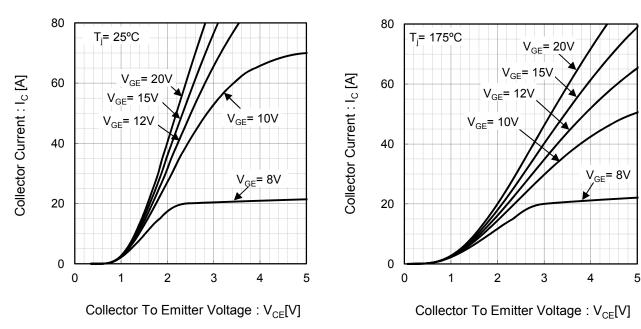


Fig.5 Typical Output Characteristics

Fig.6 Typical Output Characteristics

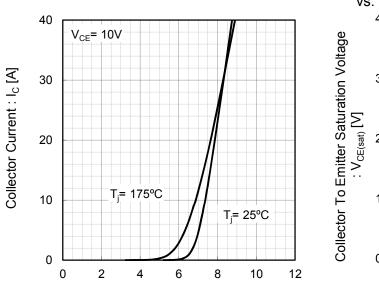
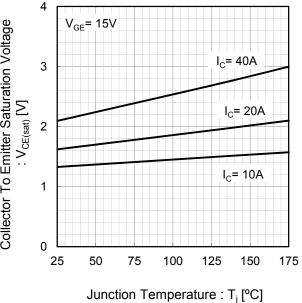


Fig.7 Typical Transfer Characteristics

Gate To Emitter Voltage : V_{GE} [V]

Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



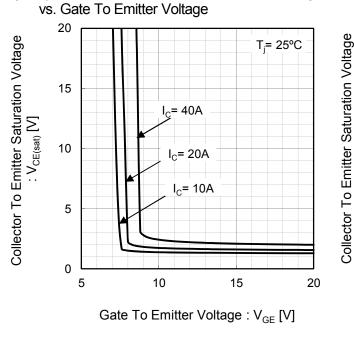
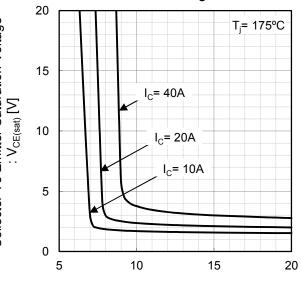


Fig.9 Typical Collector To Emitter Saturation Voltage

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage : V_{GE} [V]

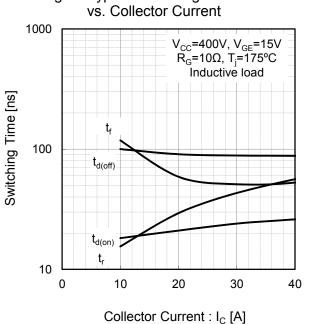
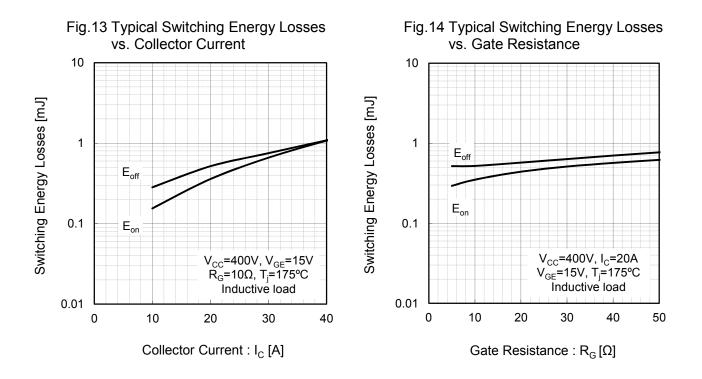


Fig.12 Typical Switching Time vs. Gate Resistance 1000 V_{CC}=400V, I_C=20A V_{GE}=15V, T_j=175°C Inductive load Switching Time [ns] 100 t_{d(off)} t_f t_{d(on)} 10 10 20 30 40 50 0 Gate Resistance : $R_G[\Omega]$

Fig.11 Typical Switching Time



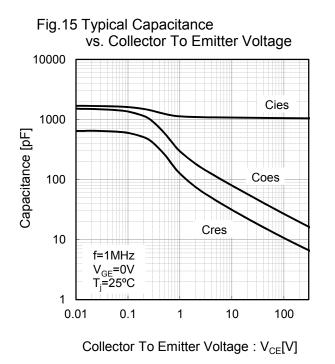
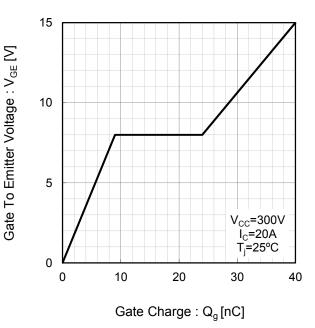


Fig.16 Typical Gate Charge



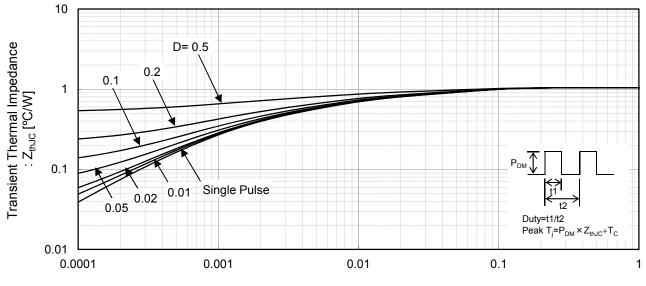


Fig.17 IGBT Transient Thermal Impedance

Pulse Width : t1[s]

●Inductive Load Switching Circuit and Waveform

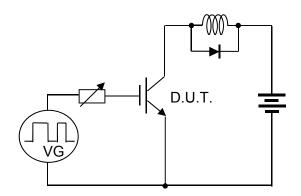
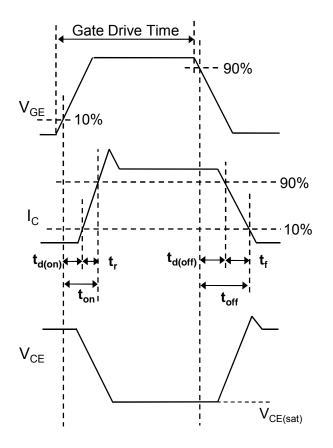


Fig.18 Inductive Load Circuit





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